





#### **40V P-CHANNEL ENHANCEMENT MODE MOSFET**

## **Product Summary**

| V <sub>(BR)DSS</sub> | R <sub>DS(on)</sub>            | I <sub>D</sub><br>T <sub>A</sub> = 25°C |  |  |
|----------------------|--------------------------------|---|--|--|
| -40V                 | 50mΩ @ V <sub>GS</sub> = -10V  | -6.0A                                   |  |  |
| -40 V                | 79mΩ @ V <sub>GS</sub> = -4.5V | -4.7A                                   |  |  |

## **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- Backlighting
- DC-DC Converters
- Power management functions

## **Features and Benefits**

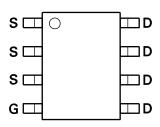
- Low on-resistance
- Fast switching speed
- "Green" component and RoHS compliant (Note 1)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

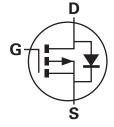
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See diagram below
- Terminals: Finish Matte Tin annealed over Copper lead frame.
   Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (approximate)







Top View



**Equivalent Circuit** 

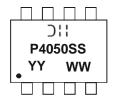
## Ordering Information (Note 1)

| Product       | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel |  |
|---------------|---------|--------------------|-----------------|-------------------|--|
| DMP4050SSS-13 | P4050SS | 13                 | 12              | 2,500             |  |

1. Diodes, Inc. defines "Green" products as those which are RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

## **Marking Information**

Note:



DII = Manufacturer's Marking P4050SS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 09 = 2009) WW = Week (01-53)





## **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic  Drain-Source voltage  Gate-Source voltage (Note 2) |                |                                      | Symbol          | Value | Unit |  |
|--|----------------|--------------------------------------|-----------------|-------|------|--|
|  |                |                                      | $V_{DSS}$       | -40   | V    |  |
|  |                |                                      | $V_{GS}$        | ±20   | V    |  |
|  |                | (Note 4)                             |                 | -6.0  |      |  |
| Continuous Drain current   | $V_{GS} = 10V$ | $T_A = 70^{\circ}C \text{ (Note 4)}$ | $I_{D}$         | -4.8  | Α    |  |
|  |                | (Note 3)                             |                 | -4.4  |      |  |
| Pulsed Drain current V <sub>GS</sub> = 10V                         |                | (Note 5)                             | I <sub>DM</sub> | -27.0 | Α    |  |
| Continuous Source current (Body diode)                             |                | (Note 4)                             | I <sub>S</sub>  | -4.0  | Α    |  |
| Pulsed Source current (Body diode)                                 |                | (Note 5)                             | I <sub>SM</sub> | -27.0 | А    |  |

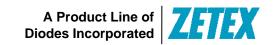
## Thermal Characteristics @TA = 25°C unless otherwise specified

| Characteristic                          | Symbol   | Value                             | Unit         |       |
|---|----------|-----------------------------------|--------------|-------|
| Power dissipation                       | (Note 3) |                                   | 1.56<br>12.5 | W     |
| Linear derating factor                  | (Note 4) | P <sub>D</sub>                    | 2.8<br>22.5  | mW/°C |
| Thermal Decistores Lunction to Ambient  | (Note 3) | Б.                                | 80           |       |
| Thermal Resistance, Junction to Ambient | (Note 4) | $R_{\theta JA}$                   | 44.5         | °C/W  |
| Thermal Resistance, Junction to Lead    | (Note 6) | $R_{	hetaJL}$                     | 35           |       |
| Operating and storage temperature range |          | T <sub>J</sub> , T <sub>STG</sub> | -55 to 150   | °C    |

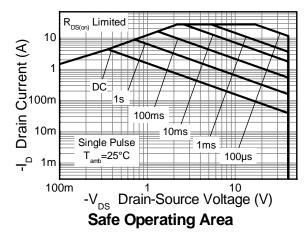
#### Notes:

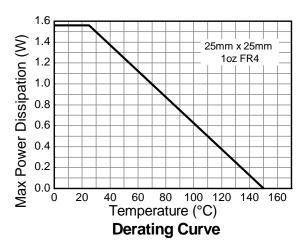
- 2. AEC-Q101  $V_{GS}$  maximum is  $\pm 16V$ .
- 3. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 4. Same as note (3), except the device is measured at t ≤ 10 sec.
  5. Same as note (3), except the device is pulsed with D= 0.02 and pulse width 300 μs. The pulse current is limited by the maximum junction temperature.
  6. Thermal resistance from junction to solder-point (at the end of the drain lead).

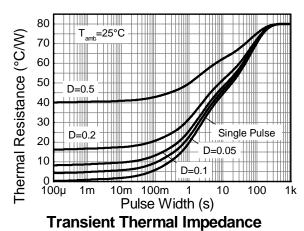


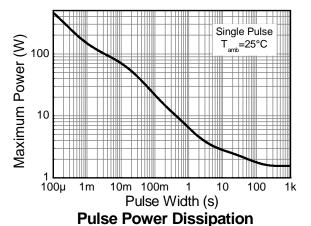


## **Thermal Characteristics**













# Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

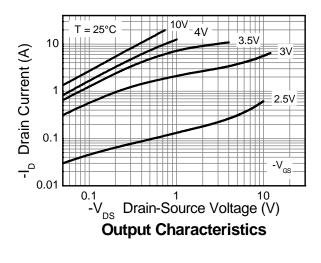
| Characteristic                              | Symbol               | Min  | Тур   | Max   | Unit | Test Co   | ndition                |
|---|----------------------|------|-------|-------|------|---|------------------------|
| OFF CHARACTERISTICS                         |                      |      |       |       |      |   |                        |
| Drain-Source Breakdown Voltage              | BV <sub>DSS</sub>    | -40  |       |       | V    | $I_D = -250 \mu A, V_{GS} =$                            | : 0V                   |
| Zero Gate Voltage Drain Current             | I <sub>DSS</sub>     | _    | _     | -0.5  | μΑ   | V <sub>DS</sub> = -40V, V <sub>GS</sub> = 0             | 0V                     |
| Gate-Source Leakage                         | I <sub>GSS</sub>     | _    | _     | ±100  | nA   | $V_{GS} = \pm 20V, V_{DS} =$                            | 0V                     |
| ON CHARACTERISTICS                          |                      |      |       |       |      |   |                        |
| Gate Threshold Voltage                      | $V_{GS(th)}$         | -1.0 |       | -3.0  | V    | $I_{D}$ = -250 $\mu$ A, $V_{DS}$ =                      | $V_{GS}$               |
| Static Drain Source On Registernes (Note 7) |                      |      | 0.038 | 0.050 | Ω    | V <sub>GS</sub> = -10V, I <sub>D</sub> = -6             | A                      |
| Static Drain-Source On-Resistance (Note 7)  | R <sub>DS</sub> (ON) |      | 0.055 | 0.079 | 77   | $V_{GS} = -4.5V, I_{D} = -5$                            | 5A                     |
| Forward Transconductance (Notes 7 & 8)      | g <sub>fs</sub>      |      | 14    | _     | S    | V <sub>DS</sub> = -15V, I <sub>D</sub> = -6/            | A                      |
| Diode Forward Voltage (Note 7)              | $V_{SD}$             | _    | -0.86 | -1.2  | V    | I <sub>S</sub> = -6A, V <sub>GS</sub> = 0V              |                        |
| Reverse recovery time (Note 8)              | t <sub>rr</sub>      |      | 18.5  | _     | ns   | 0.5 35/35 400.4/ -                                      |                        |
| Reverse recovery charge (Note 8)            | $Q_{rr}$             | _    | 15.6  | _     | nC   | $I_{S}$ = -2.5, di/dt= 100                              | UA/μS                  |
| DYNAMIC CHARACTERISTICS (Note 8)            |                      |      |       |       |      |   |                        |
| Input Capacitance                           | C <sub>iss</sub>     | _    | 674   | _     | pF   | \/ 20\/ \/  | 0)/                    |
| Output Capacitance                          | Coss                 |      | 115   | _     | pF   | V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V<br>f= 1MHz |                        |
| Reverse Transfer Capacitance                | C <sub>rss</sub>     |      | 67.7  |       | рF   | I TIVII IZ  |                        |
| Total Gate Charge (Note 9)                  | Qg                   |      | 6.9   |       | nC   | V <sub>GS</sub> = -4.5V                                 |                        |
| Total Gate Charge (Note 9)                  | $Q_g$                | _    | 13.9  | _     | nC   | ,   | V <sub>DS</sub> = -20V |
| Gate-Source Charge (Note 9)                 | Q <sub>gs</sub>      | _    | 2     | _     | nC   | V <sub>GS</sub> = -10V                                  | I <sub>D</sub> = -6A   |
| Gate-Drain Charge (Note 9)                  | $Q_{gd}$             |      | 3.4   | _     | nC   |   |                        |
| Turn-On Delay Time (Note 9)                 | t <sub>D(on)</sub>   | _    | 1.9   | _     | ns   |   |                        |
| Turn-On Rise Time (Note 9)                  | t <sub>r</sub>       | _    | 3.1   | _     | ns   | V <sub>DD</sub> = -20V, V <sub>GS</sub> = -10V          |                        |
| Turn-Off Delay Time (Note 9)                | t <sub>D(off)</sub>  | _    | 31.5  | _     | ns   | $I_{D}$ = -1A, $R_{G} \cong 6.0\Omega$                  |                        |
| Turn-Off Fall Time (Note 9)                 | t <sub>f</sub>       |      | 12.6  |       | ns   | 1   |                        |

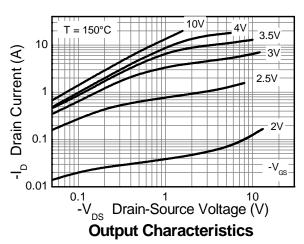
Notes:

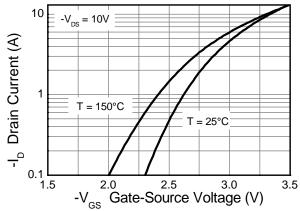
- 7. Measured under pulsed conditions. Pulse width  $\le 300 \mu s$ ; duty cycle  $\le 2\%$  8. For design aid only, not subject to production testing. 9. Switching characteristics are independent of operating junction temperatures.

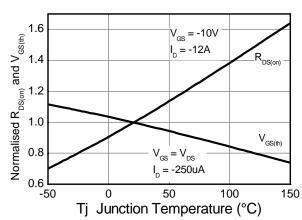


# **Typical Characteristics**



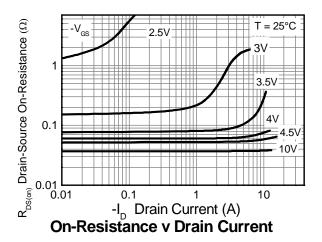


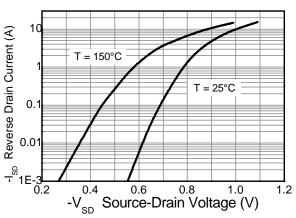




**Typical Transfer Characteristics** 

Normalised Curves v Temperature

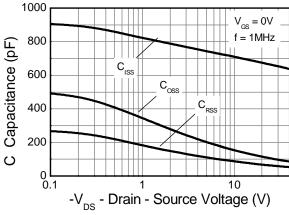




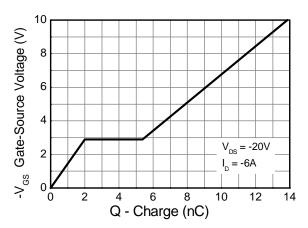
**Source-Drain Diode Forward Voltage** 



# **Typical Characteristics - continued**



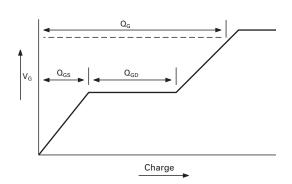
Capacitance v Drain-Source Voltage



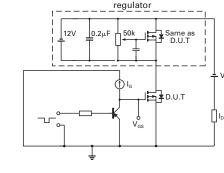
Gate-Source Voltage v Gate Charge

Current

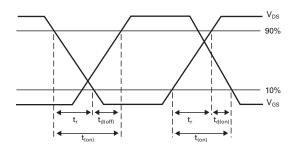
## **Test Circuits**



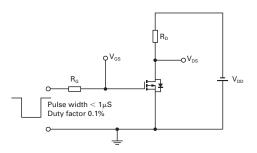
Basic gate charge waveform



Gate charge test circuit



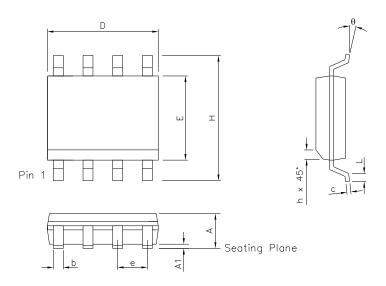
Switching time waveforms



Switching time test circuit

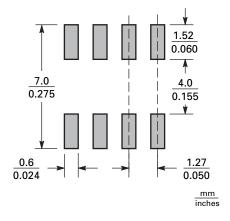


# **Package Outline Dimensions**

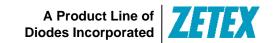


| DIM | Inc   | hes Millim |      | neters | DIM | Inches    |       | Millimeters |      |
|-----|-------|------------|------|--------|-----|-----------|-------|-------------|------|
|     | Min.  | Max.       | Min. | Max.   |     | Min.      | Max.  | Min.        | Max. |
| Α   | 0.053 | 0.069      | 1.35 | 1.75   | е   | 0.050 BSC |       | 1.27 BSC    |      |
| A1  | 0.004 | 0.010      | 0.10 | 0.25   | b   | 0.013     | 0.020 | 0.33        | 0.51 |
| D   | 0.189 | 0.197      | 4.80 | 5.00   | С   | 0.008     | 0.010 | 0.19        | 0.25 |
| Н   | 0.228 | 0.244      | 5.80 | 6.20   | θ   | 0°        | 8°    | 0°          | 8°   |
| Е   | 0.150 | 0.157      | 3.80 | 4.00   | h   | 0.010     | 0.020 | 0.25        | 0.50 |
| L   | 0.016 | 0.050      | 0.40 | 1.27   | -   | -         | -     | -           | -    |

# **Suggested Pad Layout**







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